

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J374R

### 1. Applications

• Power Management Switches

#### 2. Features

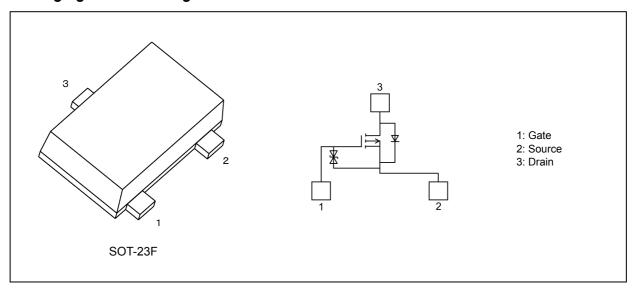
- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 4.0-V gate drive voltage.
- (3) Low drain-source on-resistance

 $R_{DS(ON)} = 71 \text{ m}\Omega \text{ (max) } (@V_{GS} = -10 \text{ V})$ 

 $R_{\rm DS(ON)} = 105 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -4.5 \ {\rm V})$ 

 $R_{DS(ON)} = 136 \text{ m}\Omega \text{ (max) (@V_{GS} = -4.0 V)}$ 

# 3. Packaging and Pin Assignment



# 4. Orderable part number

| Orderable part number | AEC-Q101 |          | Note           |          |  |
|-----------------------|----------|----------|----------------|----------|--|
| SSM3J374R,LF          | _        |          | General Use    |          |  |
| SSM3J374R,LXGF        | YES      | (Note 1) | Unintended Use | (Note 1) |  |
| SSM3J374R,LXHF        | YES      |          | Automotive Use |          |  |

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production



# 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

|                        | Characteristics |    |                    | Symbol           | Rating     | Unit |
|------------------------|-----------------|----|--------------------|------------------|------------|------|
| Drain-source voltage   |                 |    |                    | $V_{DSS}$        | -30        | V    |
| Gate-source voltage    | ,               |    |                    | $V_{GSS}$        | -20/+10    |      |
| Drain current (DC)     |                 |    | (Note 1)           | $I_D$            | -4         | Α    |
| Drain current (pulsed) |                 |    | (Note 1), (Note 2) | $I_{DP}$         | -16        |      |
| Power dissipation      | ,               |    | (Note 3)           | $P_{D}$          | 1          | W    |
| Power dissipation      | (t < 10         | s) | (Note 3)           | $P_{D}$          | 2          |      |
| Channel temperature    |                 |    |                    | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature    |                 |    |                    | T <sub>stg</sub> | -55 to 150 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  1 ms, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 6. Thermal Characteristics

| Characteristics                       |          | Symbol                | Max | Unit |
|---------------------------------------|----------|-----------------------|-----|------|
| Channel-to-ambient thermal resistance | (Note 1) | R <sub>th(ch-a)</sub> | 125 | °C/W |

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)



#### 7. Electrical Characteristics

# 7.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

| Characteristics                |          | Symbol               | Test Condition                                     | Min  | Тур. | Max  | Unit |
|--------------------------------|----------|----------------------|--|------|------|------|------|
| Gate leakage current           |          | I <sub>GSS</sub>     | V <sub>GS</sub> = -16/+10 V, V <sub>DS</sub> = 0 V | _    | _    | ±10  | μА   |
| Drain cut-off current          |          | I <sub>DSS</sub>     | V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V     | _    | _    | -1   |      |
| Drain-source breakdown voltage |          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V     | -30  | _    | _    | V    |
| Drain-source breakdown voltage | (Note 1) | V <sub>(BR)DSX</sub> | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 10 V    | -21  | _    | _    |      |
| Gate threshold voltage         | (Note 2) | V <sub>th</sub>      | $V_{DS}$ = -10 V, $I_{D}$ = -100 $\mu$ A           | -0.8 | _    | -2.0 |      |
| Drain-source on-resistance     | (Note 3) | R <sub>DS(ON)</sub>  | I <sub>D</sub> = -3.0 A, V <sub>GS</sub> = -10 V   | _    | 54   | 71   | mΩ   |
|                                |          |                      | $I_D = -2.0 \text{ A}, V_{GS} = -4.5 \text{ V}$    | _    | 80   | 105  |      |
|                                |          |                      | I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -4.0 V  | _    | 89   | 136  |      |
| Forward transfer admittance    | (Note 3) | Y <sub>fs</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.0 A   | 2.3  | 4.6  | _    | S    |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current  $(I_D)$  to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

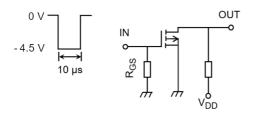
Take this into consideration when using the device.

Note 3: Pulse measurement.

# 7.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | $V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V},$                                      | _   | 280  |     | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | f = 1 MHz  |     | 40   |     |      |
| Output capacitance             | Coss             |  |     | 55   |     |      |
| Switching time (turn-on time)  | t <sub>on</sub>  | $V_{DD}$ = -15 V, $I_{D}$ = -1.0 A<br>$V_{GS}$ = 0 to -4.5 V, $R_{GS}$ = 10 $\Omega$ |     | 13   |     | ns   |
| Switching time (turn-off time) | t <sub>off</sub> | Duty ≤ 1 %, Input: tr, tf < 5 ns<br>Common source                                    |     | 22   | _   |      |

#### 7.3. Switching Time Test Circuit



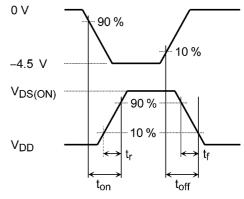


Fig. 7.3.1 Switching Time Test Circuit

Fig. 7.3.2 Input Waveform/Output Waveform

### 7.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

| Characteristics                                 | Symbol           | Test Condition                                    | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | V <sub>DD</sub> = -15 V, V <sub>GS</sub> = -10 V, | _   | 5.9  |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> | $I_D = -4.0 \text{ A}$                            | _   | 0.8  |     |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |   | _   | 1.2  |     |      |



# 7.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

| Characteristics          |         | Symbol    | Test Condition                                 | Min | Тур. | Max | Unit |
|--------------------------|---------|-----------|--|-----|------|-----|------|
| Diode forward voltage (N | Note 1) | $V_{DSF}$ | I <sub>DR</sub> = 4.0 A, V <sub>GS</sub> = 0 V | _   | 0.9  | 1.2 | V    |

Note 1: Pulse measurement.

# 8. Marking

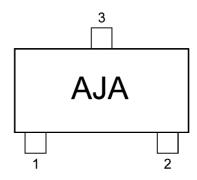


Fig. 8.1 Marking



### 9. Characteristics Curves (Note)

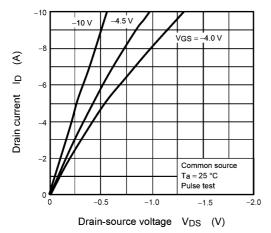


Fig. 9.1 I<sub>D</sub> - V<sub>DS</sub>

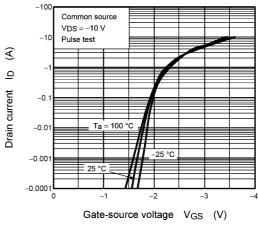


Fig. 9.2 I<sub>D</sub> - V<sub>GS</sub>

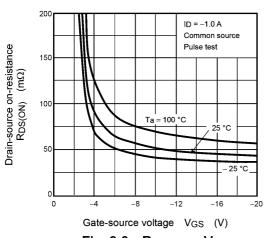


Fig. 9.3  $R_{DS(ON)}$  -  $V_{GS}$ 

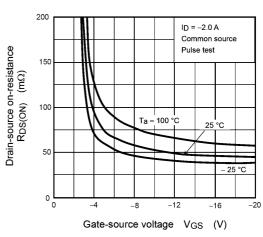


Fig. 9.4 RDS(ON) - VGS

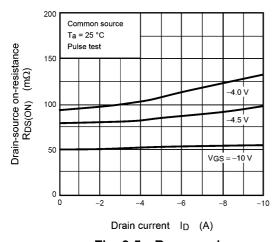


Fig. 9.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

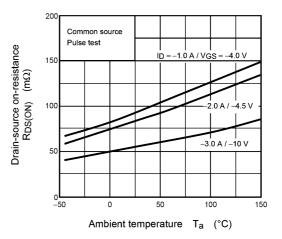
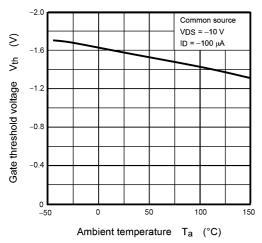
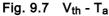


Fig. 9.6 R<sub>DS(ON)</sub> - T<sub>a</sub>







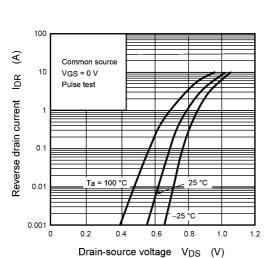


Fig. 9.9 IDR - VDS

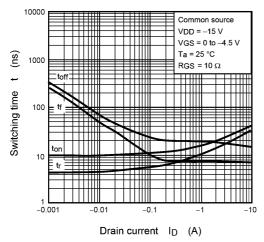


Fig. 9.11 t - I<sub>D</sub>

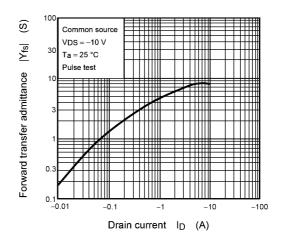


Fig. 9.8 |Y<sub>fs</sub>| - I<sub>D</sub>

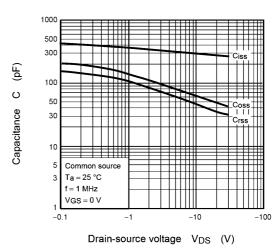


Fig. 9.10 C - V<sub>DS</sub>

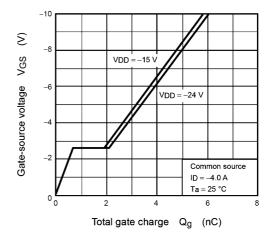
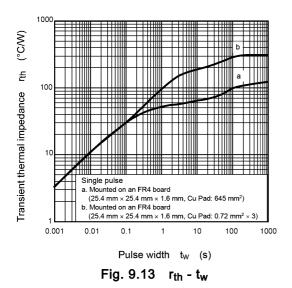


Fig. 9.12 Dynamic Input Characteristic





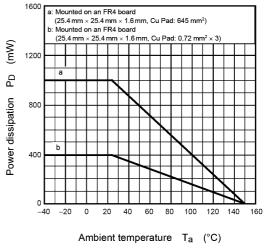


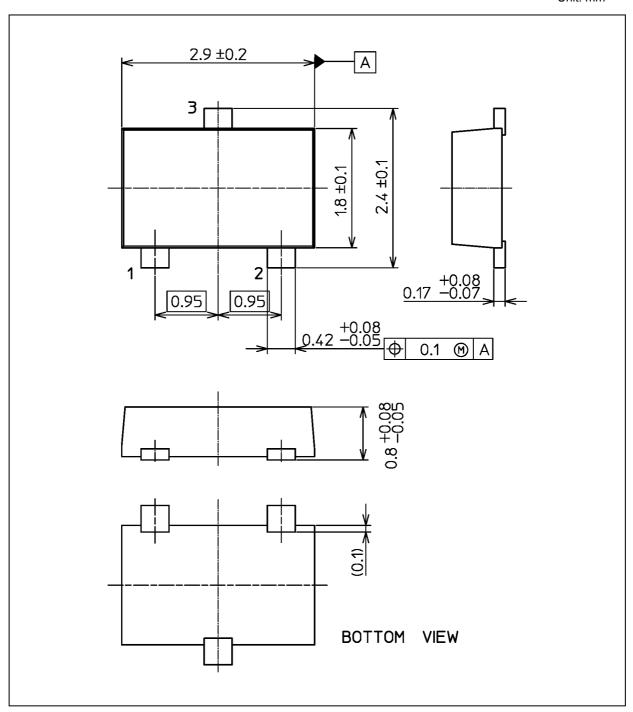
Fig. 9.14 P<sub>D</sub> - T<sub>a</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

|                   | Package Name(s) |
|-------------------|-----------------|
| TOSHIBA: 2-3Z1S   |                 |
| Nickname: SOT-23F |                 |



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